

April 1999 ADVANCE INFORMATION

FDD6030BL

N-Channel PowerTrench™ MOSFET

General Description

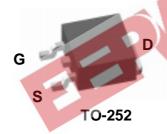
This N-Channel Logic level MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the onstate resistance and yet maintain low gate charge for superior switching performance.

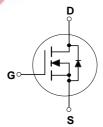
Applications

- DC/DC converter
- Motor drives

Features

- 35 A, 30 V. $R_{DS(ON)} = 0.018 \Omega$ @ $V_{GS} = 10 V$ $R_{DS(ON)} = 0.025 \Omega$ @ $V_{GS} = 4.5 V$.
- Low gate charge.
- Fast switching speed.
- High performance trench technology for extremely low R_{DS/(ON)}.





Absolute Maximum Ratings Tc=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage		30	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Maximum Drain Current -Continuous	(Note 1)	35	Α
		(Note 1a)	9	
	Maximum Drain Current -Pulsed		100	
P _D	Maximum Power Dissipation @ T _C = 25°C	(Note 1)	44	W
	$T_A = 25^{\circ}C$	(Note 1a)	2.8	
	$T_A = 25^{\circ}C$	(Note 1b)	1.3	
T_J , T_{stg}	Operating and Storage Junction Temperature	e Range	-55 to +150	°C

Thermal Characteristics

$R_{ heta$ JC	Thermal Resistance, Junction-to- Case	(Note 1)	2.8	°C/W
$R_{\theta^{JA}}$	Thermal Resistance, Junction-to- Ambient	(Note 1b)	96	°C/W

Package Marking and Ordering Information

Device Marking	Device Marking Device		Tape width	Quantity
FDD6030BL	FDD6030BL	13"	16mm	2500

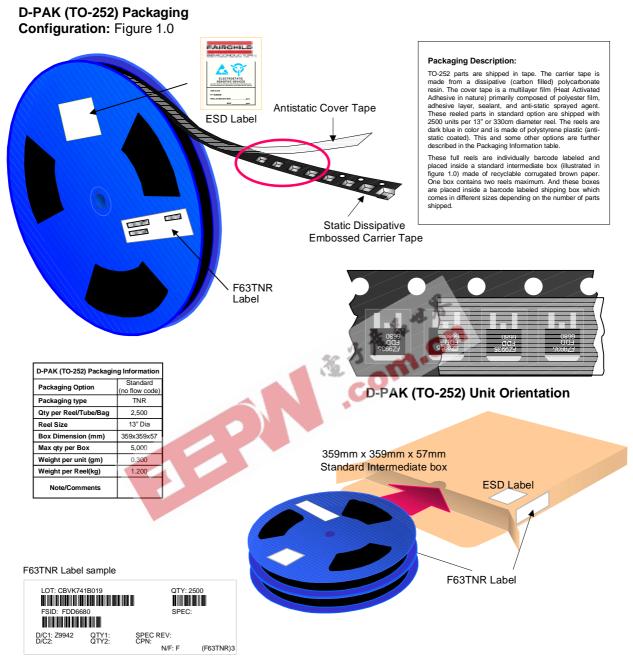
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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
055.01	LADA OTERIOTION					
	IARACTERISTICS	Tu ava ana				
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
		163 20 1, 183 0 1			100	1
	ARACTERISTICS (Note 2) Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1		3	V
ON CHA V _{GS(TH)} R _{DS(ON)}	ARACTERISTICS (Note 2)	, , ,	1			
V _{GS(TH)} R _{DS(ON)}	ARACTERISTICS (Note 2) Gate Threshold Voltage Static Drain-Source	$V_{DS} = V_{GS}, I_D = 250 \mu A$ $V_{GS} = 10 \text{ V}, I_D = 9 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}$	·	<u> </u>	3 0.018	V
V _{GS(TH)} R _{DS(ON)}	ARACTERISTICS (Note 2) Gate Threshold Voltage Static Drain-Source On-Resistance	$V_{DS} = V_{GS}, I_D = 250 \mu A$ $V_{GS} = 10 \text{ V}, I_D = 9 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 7.5 \text{ A}$ RISTICS AND MAXIMUM	·		3 0.018	V

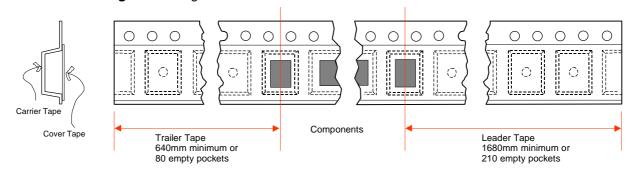


Scale 1 : 1 on letter size paper

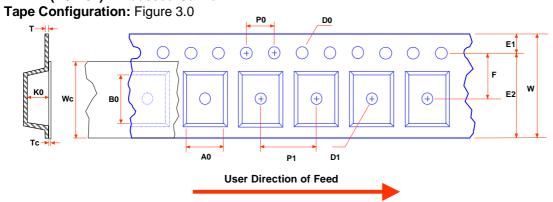
2. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%



TO-252 (D-PAK) Tape Leader and Trailer Configuration: Figure 2.0

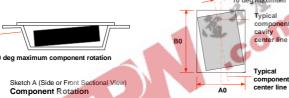


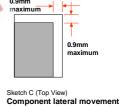




Dimensions are in millimeter														
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
TO252 (24mm)	6.90 +/-0.10	10.50 +/-0.10	16.0 +/-0.3	1.55 +/-0.05	1.5 +/-0.10	1.75 +/-0.10	14.25 min	7.50 +/-0.10	8.0 +/-0.1	4 .0 +/-0.1	2.65 +/-0.10	0.30 +/-0.05	13.0 +/-0.3	0.06 +/-0.02

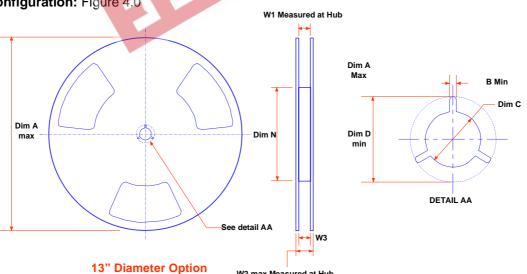
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).





Sketch B (Top View)
Component Rotation

D-PAK (TO-252) Reel Configuration: Figure 4.0



	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
164mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.646 +0.078/-0.000 16.4 +2/0	0.882 22.4	0.626 – 0.764 15.9 – 19.4

W2 max Measured at Hub

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